

Serial No. 10/739,229

Atty. Docket 29936/39870

AMENDMENTS TO THE SPECIFICATION

Please replace paragraph [0008] with the following amended paragraph:

Fig. 1C is a cross-sectional view illustrating a state that the gate oxide 20 and a device isolation film are formed by performing a patterning process, a self-aligned contact oxidation process, ~~an HDP~~ a High Density Plasma (HDP) oxide film burying process, and a nitride film removing process for forming a device isolation film.

Please replace the Abstract with the following amended Abstract:

The present invention provides a method for forming a gate oxide film of a semiconductor device including comprising the steps of; forming a gate oxide film and a polysilicon film sequentially on a semiconductor substrate; performing a nitrogen ion implantation process ~~for the semiconductor substrate including~~ after the formation of the gate oxide film and the polysilicon film; performing a thermal treatment process to form barrier layers by combination of oxides and nitrogen at an interface between the semiconductor substrate and the gate oxide film, and at an interface between the gate oxide film and the polysilicon film; and forming a nitride on the polysilicon film.